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1.0 Key Features

- Complete programmable control via l²C[™]-bus
- Selectable CMOS or PECL compatible outputs
- External feedback loop capability allows genlocking
- Tunable VCXO loop for jitter attenuation

2.0 General Description

The FS6131-01 is a monolithic CMOS clock generator/regenerator IC designed to minimize cost and component count in a variety of electronic systems. Via the I²C-bus interface, the FS6131-01 can be adapted to many clock generation requirements.

The ability to tune the on-board voltage-controlled crystal oscillator (VCXO), the length of the reference and feed-back dividers, their granularity, and the flexibility of the post divider make the FS6131-01 the most flexible stand-alone phase-locked loop (PLL) clock generator available.

3.0 Applications

- Frequency synthesis
- Line-locked and genlock applications
- Clock multiplication
- Telecom jitter attenuation





Table 1: Pin Descriptions

Key: AI = Analog Input; AO = Analog Output; DI = Digital Input; DI^{U} = Input with Internal Pull-Up; DI_{D} = Input with Internal Pull-Down; DIO = Digital Input/Output; DI-3 = Three-Level Digital Input, DO = Digital Output; P = Power/Ground; # = Active Low pin

Pin	Туре	Name	Description
1	DI	SCL	Serial interface clock (requires an external pull-up)
2	DIO	SDA	Serial interface data input/output (requires an external pull-up)
3	DI	ADDR	Address select bit (see Section 5.2.1)
4	Р	VSS	Ground
5	AI	XIN	VCXO feedback
6	AO	XOUT	VCXO drive
7	AI	XTUNE	VCXO tune
8	Р	VDD	Power supply (+5V)
9	DIO	LOCK/IPRG	Lock indicator / PECL current drive programming
10	AI	EXTLF	External loop filter
11	Р	VSS	Ground
12	DI	REF	Reference frequency input
13	DI	FBK	Feedback input
14	Р	VDD	Power supply (+5V)
15	DO	CLKP	Differential clock output (+)
16	DO	CLKN	Differential clock output (-)

4.0 Functional Block Description

4.1 Main Loop PLL

The main loop phase locked loop (ML-PLL) is a standard phase- and frequency- locked loop architecture. As shown in **Error! Reference source not found.**, the ML-PLL consists of a reference divider, a phase-frequency detector (PFD), a charge pump, an internal loop filter, a voltage-controlled oscillator (VCO), a feedback divider, and a post divider.

During operation, the reference frequency (f_{REF}), generated by either the on-board crystal oscillator or an external frequency source, is first reduced by the reference divider. The integer value that the frequency is divided by is called the modulus, and is denoted as N_R for the reference divider. The divided reference is then fed into the PFD.

The PFD controls the frequency of the VCO (f_{VCO}) through the charge pump and loop filter. The VCO provides a high-speed, low noise, continuously variable frequency clock source for the ML-PLL. The output of the VCO is fed back to the PFD through the feedback divider (the modulus is denoted by N_F) to close the loop.

The PFD will drive the VCO up or down in frequency until the divided reference frequency and the divided VCO frequency appearing at the inputs of the PFD are equal. The input/output relationship between the reference frequency and the VCO frequency is

$$\frac{f_{VCO}}{N_E} = \frac{f_{REF}}{N_R}$$

If the VCO frequency is used as the PLL output frequency (folk) then the basic PLL equation can be rewritten as

$$f_{CLK} = f_{REF} \left(\frac{N_F}{N_R} \right)$$

4.1.1. Reference Divider

The reference divider is designed for low phase jitter. The divider accepts either the output of either the crystal loop (the VCXO output) or an external reference frequency, and provides a divided-down frequency to the PFD. The reference divider is a 12-bit divider, and can be programmed for any modulus from 1 to 4095. See both Table 3 and Table 8 for additional programming information.

4.1.2. Feedback Divider

The feedback divider is based on a dual-modulus pre-scaler technique. The technique allows the same granularity as a fully programmable feedback divider, while still allowing the programmable portion to operate at low speed. A high-speed pre-divider (also called a prescaler) is placed between the VCO and the programmable feedback divider because of the high speeds at which the VCO can operate. The dual-modulus technique insures reliable operation at any speed that the VCO can achieve and reduces the overall power consumption of the divider.

For example, a fixed divide-by-eight could be used in the feedback divider. Unfortunately, a divide-by-eight would limit the effective modulus of the feedback divider path to multiples of eight. The limitation would restrict the ability of the PLL to achieve a desired input-frequency-to-output frequency ratio without making both the reference and feedback divider values comparatively large. Large divider moduli are generally undesirable due to increased phase jitter.



To understand the operation, refer to **Error! Reference source not found.**. The M-counter (with a modulus of M) is cascaded with the dual-modulus pre-scaler. If the prescaler modulus were fixed at N, the overall modulus of the feedback divider chain would be MXN. However, the A-counter causes the pre-scaler modulus to be altered to N+1 for the first A outputs of the pre-scaler. The A-counter then causes the dual-modulus prescaler to revert to a modulus of N until the M-counter reaches its terminal state and resets the entire divider. The overall modulus can be expressed as

$$A(N+1) + N(M-A)$$

where $M \ge A$, which simplifies to

 $M \times N + A$

4.1.3. Feedback Divider Programming

The requirement that $M \ge A$ means that the feedback divider can only be programmed for certain values below a divider modulus of 56. The selection of divider values is listed in Table 2.

If the desired feedback divider is less than 56, find the divider value in the table. Follow the column up to find the A-counter program value. Follow the row to the left to find the M-counter value.

Above a modulus of 56, the feedback divider can be programmed to any value up to 16383. See both Table 3 and Table 8 for additional programming information.

M-Counter:	A-counter: FBKDIV[2:0]								
FBKDIV[13:3]	000	001	010	011	100	101	110	111	
0000000001	8	9	-	-	-	-	-	-	
0000000010	16	17	18	-	-	-	-	-	
0000000011	24	25	26	27	-	-	-	-	
0000000100	32	33	34	35	36	-	-	-	
0000000101	40	41	42	43	44	45	-	-	
0000000110	48	49	50	51	52	53	54	-	
0000000111	56	57	58	59	60	61	62	63	
		Feedback Divider Modulus							

Table 2: Feedback Modulus Below 56

4.1.4. Post Divider

The post divider consists of three individually programmable dividers, as shown in Error! Reference source not found.



The moduli of the individual dividers are denoted as N_{P1} , N_{P2} , and N_{P3} , and together they make up the array modulus N_{Px} .

$$N_{Px} = N_{P1} \times N_{P2} \times N_{P3}$$

The post divider performs several useful functions. First, it allows the VCO to be operated in a narrower range of speeds compared to the variety of output clock speeds that the device is required to generate. Second, it changes the basic PLL equation to

$$f_{CLK} = f_{REF} \left(\frac{N_F}{N_R} \right) \left(\frac{1}{N_{Px}} \right)$$

The extra integer in the denominator permits more flexibility in the programming of the loop for many applications where frequencies must be achieved exactly.

Note that a nominal 50/50 duty factor is preserved for selections which have an odd modulus.

4.2 Phase Adjust and Sampling

In line-locked or genlocked applications, it is necessary to know the exact phase relation of the output clock relative to the input clock. Since the VCO is included within the feedback loop in a simple PLL structure, the VCO output is exactly phase aligned with the input clock. Every cycle of the input clock equals $N_{\text{P}}/N_{\text{F}}$ cycles of the VCO clock.



The addition of a post divider, while adding flexibility, makes the phase relation between the input and output clock unknown because the post divider is outside the feedback loop.



4.2.1. Clock Gobbler (Phase Adjust)

The clock gobbler circuit takes advantage of the unknown relationship between input and output clocks to permit the adjustment of the CLKP/CLKN output clock phase relative to the REF input. The clock gobbler circuit removes a VCO clock pulse before the pulse clocks the post divider. In this way, the phase of the output clock can be slipped until the output phase is aligned with the input clock phase.

To adjust the phase relationship, switch the feedback divider source to the post divider input via the FBKDSRC bit, and toggle the GBL register bit. The clock gobbler output clock is delayed by one VCO clock period for each transition of the GBL bit from zero to one.

4.2.2. Phase Alignment

To maintain a fixed phase relation between input and output clocks, the post divider must be placed inside the feedback loop. The source for the feedback divider is obtained from the output of the post divider via the FBKDSRC switch. In addition, the feedback divider must be dividing at a multiple of the post divider.



4.2.3. Phase Sampling and Initial Alignment

However, the ability to adjust the phase is useless without knowing the initial relation between output and input phase. To aid in the initial synchronization of the output phase to input phase, a phase align "flag" makes a transition (zero to one or one to zero) when the output clock phase becomes aligned with the feedback source phase. The feedback source clock is, by definition, locked to the input clock phase.

First, the FS6131 is used to sample the output clock with the feedback source clock and set/clear the phase align flag when the two clocks match to within a feedback source clock period. Then, the clock gobbler is used to delay the output phase relative to the input phase one VCO clock at a time until a transition on the flag occurs. When a transition occurs, the output and input clocks are phase aligned.

To enter this mode, set STAT[1] to one and clear STAT[0] to zero. If the CMOS bit is set to one, the LOCK/IPRG pin can display the flag. The flag is always available under software control by reading back the STAT[1] bit, which will be overwritten by the flag in this mode.

4.2.4. Feedback Divider Monitoring

The feedback divider clock can be brought out the LOCK/IPRG pin independent of the output clock to allow monitoring of the feedback divider clock. To enter this mode, set both the STAT[1] and STAT[0] bits to one. The CMOS bit must also be set to one to enable the LOCK/IPRG pin as an output.

4.3 Loop Gain Analysis

For applications where an external loop filter is required, the following analysis example can be used to determine loop gain and stability.

The loop gain of a PLL is the product of all of the gains within the loop.

Set the charge pump current:	$I_{chgpump} = 10 \mu A$
Set the loop filter values:	$\begin{split} R_{LF} = &15k\Omega\\ C_1 = &0.015\mu F\\ C_2 = &220pF \end{split}$
Set the VCO gain (VCOSPD):	$A_{VCO} = 230 MHz / V$
Set the feedback divider:	$N_{F} = 3500$
Set the reference frequency (at the input to the phase detector):	$f_{REF} = 20 kHz$

The transfer function of the phase detector and charge pump combination is (in A/rad):

$$K_{PD} = \frac{I_{chgpump}}{2\pi}$$

The transfer function of the loop filter is (in V/A):

$$K_{LF}(s) = \frac{1}{sC_2 + \left(\frac{1}{R_{LF} + \left(\frac{1}{sC_1}\right)}\right)}$$

The VCO transfer function (in rad/s, and accounting for the phase integration that occurs in the VCO) is:

$$K_{VCO}(s) = 2\pi A_{VCO} \frac{1}{s}$$

The transfer function of the feedback divider is:

$$K_F = \frac{1}{N_F}$$

Finally, the sampling effect that occurs in the phase detector is accounted for by:

$$K_{SAMP}(s) = \left(\frac{1 - e^{-\left(\frac{s}{f_{REF}}\right)}}{s}\right) f_{REF}$$

The loop gain of the PLL is:

$$K_{LOOP}(s) = K_{PD}K_{LF}(s)K_{VCO}(s)K_FK_{SAMP}(s)$$



The loop phase angle is:

$$\Theta_i = \arg \left[K_{LOOP}(j 2\pi f_i) \right]$$



A Nyquist plot of gain vs. amplitude is shown below.



4.4 Voltage-Controlled Crystal Oscillator

The VCXO provides a tunable, low-jitter frequency reference for the rest of the FS6131 system components. Loading capacitance for the crystal is internal to the device. No external components (other than the resonator itself) are required for operation of the VCXO.

The resonator loading capacitance is adjustable under register control. This feature permits factory coarse tuning of inexpensive resonators to the necessary precision for digital video applications. Continuous fine-tuning of the VCXO frequency is accomplished by

varying the voltage on the XTUNE pin. The total change (from one extreme to the other) in effective loading capacitance is 1.5pF nominal, and the effect is shown in **Error! Reference source not found.** The oscillator operates the crystal resonator in the parallelresonant mode. Crystal warping, or the "pulling" of the crystal oscillation frequency, is accomplished by altering the effective load capacitance presented to the crystal by the oscillator circuit. The actual amount that changing the load capacitance alters the oscillator frequency will be dependent on the characteristics of the crystal as well as the oscillator circuit itself.

The motional capacitance of the crystal (usually referred to by crystal manufacturers as C_1), the static capacitance of the crystal (C_0) and the load capacitance (C_L) of the oscillator determine the warping capability of the crystal in the oscillator circuit. A simple formula to determine the total warping capability of a crystal is

$$\Delta f(ppm) = \frac{C_1 \times (C_{L2} - C_{L1}) \times 10^6}{2 \times (C_0 + C_{L2}) \times (C_0 + C_{L1})}$$

where CL1 and CL2 are the two extremes of the applied load capacitance obtained from Table 11.

Example: A crystal with the following parameters is used with the FS6131. The total coarse tuning range is:

C1=0.02pF, C0=5.0pF, CL1=10.0pF, CL2=22.66pF

$$\Delta f = \frac{0.02 \times (22.66 - 10) \times 10^6}{2 \times (5 + 22.66) \times (5 + 10)} = 305 \, ppm$$

4.4.1. VCXO Tuning

The VCXO may be coarse tuned by a programmable adjustment of the crystal load capacitance via the XCT[3:0] control bits. See Table 11 for the control code and the associated loading capacitance.

The actual amount of frequency warping caused by the tuning capacitance will depend on the crystal used. The VCXO tuning capacitance includes an external 6pF load capacitance (12pF from the XIN pin to ground and 12pF from the XOUT pin to ground). The fine tuning capability of the VCXO can be enabled by setting the XLVTEN bit to a one, or disabled by setting it to a zero.

Error! Reference source not found. shows the typical effect of the coarse and fine tuning mechanisms. The total coarse tune range is about 350ppm. The difference in VCXO frequency in parts per million (ppm) is shown as the fine tuning voltage on the XTUNE pin varies from 0V to 5V. Note that as the crystal load capacitance is increased the VCXO frequency is pulled somewhat less with each coarse step, and the fine tuning range decreases. The fine tuning range always overlaps a few coarse tuning ranges, eliminating the possibility of holes in the VCXO response. The different crystal warping characteristics may change the scaling on the Y-axis, but not the overall characteristic of the curves.



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4.5 Crystal Loop

The crystal loop is designed to attenuate the jitter on a highly jittered, low-Q, low frequency reference. The crystal loop can also maintain a constant frequency output into the main loop if the low frequency reference is intermittent.

The crystal loop consists of a voltage-controllable crystal oscillator (VCXO), a divider, a PFD, and a charge pump that tunes the VCXO to a frequency reference. The frequency reference is phase-locked to the divided frequency of an external, high-Q, jitter-free crystal, thereby locking the VCXO to the reference frequency. The VCXO can continue to run off the crystal even if the frequency reference becomes intermittent.

4.5.1. Locking to an External Frequency Source

When the crystal loop is synchronized to an external frequency source, the FS6131 can monitor the crystal loop and detect if the loop unlocks from the external source. The crystal loop tries to drive to zero frequency if the external source is dropped, and sets a lock status error flag.

The crystal loop can also detect if the VCXO has dropped out of the fine tune range, requiring a change to the coarse tune. The lock status also latches the direction the loop went out of range (high or low) when the loop became unlocked.

4.5.1.1 Crystal Loop Lock Status Flag

To enable this mode, clear the STAT[1] and STAT[0] bits to zero. If the CMOS bit is set to one, the LOCK/IPRG pin will be low if the crystal loop becomes unlocked. The flag is always available under software control by reading back the STAT[1] bit, which is overwritten with the status flag (low = unlocked) in this mode (see Table 6).

4.5.1.2 Out-Of-Range High/Low

The direction the loop has gone out-of-range can be determined by clearing STAT[1] to zero and setting STAT[0] bit to one. If the CMOS bit is set to one, the LOCK/IPRG pin will go high if the crystal loop went out of range high. If the pin goes to a logic-low, the loop went out of range low.

The out-of-range information is also available under software control by reading back the STAT[1] bit, which is overwritten by the flag (high = outof-range high, low = out-of-range low) in this mode. The bit is set or cleared only if the crystal loop loses lock (see Table 6).

4.5.1.3 Crystal Loop Disable

The crystal loop is disabled by setting the XLPDEN bit to a logic-high (1). The bit disables the charge pump circuit in the loop.

Setting the XLPDEN bit low (0) permits the crystal loop to operate as a control loop.

4.6 Connecting the FS6131 to an External Reference Frequency

If a crystal oscillator is not used, tie XIN to ground and shut down the crystal oscillator by setting XLROM[2:0]=1.

The REF and FBK pins do not have pull-up or pull-down current, but do have a small amount of hysteresis to reduce the possibility of extra edges. Signals may be AC-coupled into these inputs with an external DC-bias circuit to generate a DC-bias of 2.5V. Any reference or feedback signal should be square for best results, and the signals should be rail-to-rail. Unused inputs should be grounded to avoid unwanted signal injection.

4.7 Differential Output Stage

The differential output stage supports both CMOS and pseudo-ECL (PECL) signals. The desired output interface is chosen via the program registers (see Table 4).

If a PECL interface is used, the transmission line is usually terminated using a Thévenin termination. The output stage can only sink current in the PECL mode, and the amount of sink current is set by a programming resistor on the LOCK/IPRG pin. The ratio of IPRG current to output drive current is shown in Figure 12. Source current is provided by the pull-up resistor that is part of the Thévenin termination.



5.0 I²C-bus Control Interface

This device is a read/write slave device meeting all Philips I₂C-bus specifications except a "general call." The bus has to be controlled by a master device that generates the serial clock SCL, controls bus access and generates the START and STOP conditions while the device works as a slave. Both master and slave can operate as a transmitter or receiver, but the master device determines which mode is activated. A device that sends data onto the bus is defined as the transmitter, and

a device receiving data as the receiver. I₂C-bus logic levels noted herein are based on a percentage of the power supply (V_{DD}). A logic-one corresponds to a nominal voltage of V_{DD}, while a logic-zero corresponds to ground (V_{SS}).

5.1 Bus Conditions

Data transfer on the bus can only be initiated when the bus is not busy. During the data transfer, the data line (SDA) must remain stable whenever the clock line (SCL) is high. Changes in the data line while the clock line is high will be interpreted by the device as a START or STOP condition. The following bus conditions are defined by the l₂C-bus protocol.

5.1.1. Not Busy

Both the data (SDA) and clock (SCL) lines remain high to indicate the bus is not busy.

5.1.2. START Data Transfer

A high to low transition of the SDA line while the SCL in-put is high indicates a START condition. All commands to the device must be preceded by a START condition.

5.1.3. STOP Data Transfer

A low to high transition of the SDA line while SCL is held high indicates a STOP condition. All commands to the device must be followed by a STOP condition.

5.1.4. Data Valid

The state of the SDA line represents valid data if the SDA line is stable for the duration of the high period of the SCL line after a START condition occurs. The data on the SDA line must be changed only during the low period of the SCL signal. There is one clock pulse per data bit.

Each data transfer is initiated by a START condition and terminated with a STOP condition. The number of data bytes transferred between START and STOP conditions is determined by the master device, and can continue indefinitely. However, data that is overwritten to the device after the first eight bytes will overflow into the first register, then the second, and so on, in a first-in, first-overwritten fashion.

5.1.5. Acknowledge

When addressed, the receiving device is required to generate an acknowledge after each byte is received. The master device must generate an extra clock pulse to coincide with the acknowledge bit. The acknowledging device must pull the SDA line low during the high period of the master acknowledge clock pulse. Setup and hold times must be taken into account.

The master must signal an end of data to the slave by not generating an acknowledge bit on the last byte that has been read (clocked) out of the slave. In this case, the slave must leave the SDA line high to enable the master to generate a STOP condition.

5.2 l²C-bus Operation

All programmable registers can be accessed randomly or sequentially via this bi-directional two wire digital interface. The crystal oscillator does not have to run for communication to occur.

The device accepts the following I₂C-bus commands.

5.2.1. Slave Address

After generating a START condition, the bus master broadcasts a seven-bit slave address followed by a R/W bit. The address of the device is:

A6	A5	A4	A3	A2	A1	A0
1	0	1	1	Х	0	0

where X is controlled by the logic level at the ADDR pin. The variable ADDR bit allows two different FS6131 devices to exist on the same bus. Note that every device on an I₂C-bus must have a unique address to avoid bus conflicts. The default address sets A2 to 0 via the pull-down on the ADDR pin.

5.2.2. Random Register Write Procedure

Random write operations allow the master to directly write to any register. To initiate a write procedure, the R/W bit that is transmitted after the seven-bit device address is a logic-low. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is written into the slave's address pointer. Following an acknowledge by the slave, the master is allowed to write eight bits of data into the addressed register. A final acknowledge is returned by the device, and the master generates a STOP condition.

If either a STOP or a repeated START condition occurs during a register write, the data that has been transferred is ignored.

5.2.3. Random Register Read Procedure

Random read operations allow the master to directly read from any register. To perform a read procedure, the R/W bit that is transmitted after the seven-bit address is a logic-low, as in the register write procedure. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is then written into the slave's address pointer.

Following an acknowledge by the slave, the master generates a repeated START condition. The repeated START terminates the write procedure, but not until after the slave's address pointer is set. The slave address is then resent, with the R/W bit set this time to a logic-high, indicating to the slave that data will be read. The slave will acknowledge the device address, and then transmits the eight-bit word. The master does not acknowledge the transfer but does generate a STOP condition.

5.2.4. Sequential Register Write Procedure

Sequential write operations allow the master to write to each register in order. The register pointer is automatically incremented after each write. This procedure is more efficient than the random register write if several registers must be written.

To initiate a write procedure, the R/W bit that is transmitted after the seven-bit device address is a logic-low. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is written into the slave's address pointer. Following an acknowledge by the slave, the master is allowed to write up to eight bytes of data into the addressed register before the register address pointer overflows back to the beginning address. An acknowledge by the device between each byte of data must occur before the next data byte is sent.

Registers are updated every time the device sends an acknowledge to the host. The register update does not wait for the STOP condition to occur. Registers are therefore updated at different times during a sequential register write.

5.2.5. Sequential Register Read Procedure

Sequential read operations allow the master to read from each register in order. The register pointer is automatically incremented by one after each read. This procedure is more efficient than the random register read if several registers must be read.

To perform a read procedure, the R/W bit that is transmitted after the seven-bit address is a logic-low, as in the register write procedure. This indicates to the addressed slave device that a register address will follow after the slave device acknowledges its device address. The register address is then written into the slave's address pointer.

Following an acknowledge by the slave, the master generates a repeated START condition. The repeated START terminates the write procedure, but not until after the slave's address pointer is set. The slave address is then resent, with the R/W bit set this time to a logic-high, indicating to the slave that data will be read. The slave will acknowledge the device address, and then transmits all eight bytes of data starting with the initial addressed register. The register address pointer will overflow if the initial register address is larger than zero. After the last byte of data, the master does not acknowledge the transfer but does generate a STOP condition.







6.0 Programming Information

All register bits are cleared to zero on power-up. All register bits may be read back as written except STAT[1] (Bit 63).

Table 3: Regi	ster Map							
Address	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
	STAT[1] (Bit 63)	STAT[0] (Bit 62)	XLVTEN (Bit 61)	CMOS (Bit 60)	XCT[3] (Bit 59)	XCT[2] (Bit 58)	XCT[1] (Bit 57)	XCT[0] (Bit 56)
Dute 7	00 = Crystal Lo	op – Lock Status	0 = Fine Tune	0 - PECI				
Byle /	01 = Crystal Loop – Out of Range		Inactive	0-1202		VCXO Coa	arse Tune	
	10 = Main Loop	o – Phase Status	1 = Fine Tune	1 = CMOS, Lock		See Ta	ble 11	
	11 = Feedbac	k Divider Output	Active	Status				
	XLPDEN (Bit 55)	XLSWAP (Bit 54)	XLCP[1] (Bit 53)	XLCP[0] (Bit 52)	XLROM[2] (Bit 51)	XLROM[1] (Bit 50)	XLROM[0] (Bit 49)	GBL (Bit 48)
Byte 6	0 = Crystal Loop Operates	0 = Use with External VCXO	00 = 01 =	1.5µА : 5µА		Crvstal Loop Control		0 = No Clock Phase Adjust
	1 = Crystal Loop	1 = Use with	10 =	8µA		See Table 10		1 = Clock Phase
	Powered Down	Internal VCXO	11 =	24µA				Delay
	OUTMUX[1] (Bit 47)	OUTMUX[0] (Bit 46)	OSCTYPE (Bit 45)	VCOSPD (Bit 44)	LFTC (Bit 43)	EXTLF (Bit 42)	MLCP[1] (Bit 41)	MLCP[0] (Bit 40)
	00 = VC	CO Output	0 = Low Phase	0 = High Speed	0 = Short Time	0 = Internal Loop	00 = 1.5µA	
Byte 5	01 = Referenc	e Divider Output	Jitter Oscillator Range		Constant	Filter	01 = 5µA	
	10 = Phase Detector Input 11 = VCXO Output		1 = FS6031 Oscillator	1 = Low Speed Range	1 = Long Time Constant	1 = External Loop Filter	10 = 8µA	
							11 =	24µA
	FBKDSRC[1] (Bit 39)	FBKDSRC[0] (Bit 38)	FBKDIV[13] (Bit 37)	FBKDIV[12] (Bit 36)	FBKDIV[11] (Bit 35)	FBKDIV[10] (Bit 34)	FBKDIV[9] (Bit 33)	FBKDIV[8] (Bit 32)
Dute (00 = Post Divider Output 01 = FBK Pin		8192	4096	2048	1024	512	256
Byle 4			4030 2040					
	10 = Post	Divider Input	M Counter					
	11 = 1	-BK Pin						
Buto 3	FBKDIV[7] (Bit 31)	FBKDIV[6] (Bit 30)	FBKDIV[5] (Bit 29)	FBKDIV[4] (Bit 28)	FBKDIV[3] (Bit 27)	FBKDIV[2] (Bit 26)	FBKDIV[1] (Bit 25)	FBKDIV[0] (Bit 24)
Byles	128	64	32	16	8	4	2	1
			M Counter				A Counter – See Table 2	
			POST3[1] (Bit 21)	POST3[1] (Bit 20)	POST2[1] (Bit 19)	POST2[0] (Bit 18)	POST1[1] (Bit 17)	POST1[0] (Bit 16)
Byte 2	Beserved (0)	Reserved (0)	00 = Div	vide by 1	00 = Divide by 1		00 = Divide by 1	
			01 = Div	vide by 3	01 = Divide by 3		01 = Divide by 2	
			10 = Div	vide by 5	10 = Divide by 5		10 = Divide by 4	
			11 = Div	vide by 4	11 = Divi	ide by 4	11 = Di	vide by 8
	PDFBK (Bit 15)	PDREF (Bit 14)	SHUT (Bit 13)	REFDSRC (Bit 12)	REFDIV[11] (Bit 11)	REFDIV[10] (Bit 10)	REFDIV[9] (Bit 9)	REFDIV[8] (Bit 8)
Byte 1	0 = Feedback Divider	0 = Reference Divider	0 = Main Loop Operates	0 = VCXO	2048	1024	512	256
	1 = FBK Pin	1 = REF Pin	1 = Main Loop Powered Down	1 = Ref Pin				
Byte 0	BEFDIV[7] (Bit 7)	REFDIV[6] (Bit 6)	REFDIV[5] (Bit 5)	REFDIV[4] (Bit 4)	REFDIV[3] (Bit 3)	REFDIV[2] (Bit 2)	REFDIV[1] (Bit 1)	REFDIV[0] (Bit 0)
	128	64	32	16	8	4	2	1

Table 4: Device Configuration Bits

Name	Description				
DEEDODO	REFerence Divider	^r SouRCe			
	Bit = 0	Crystal Oscillator (VCXO)			
	Bit = 1 REF pin				
снит	main loop SHUT down select				
(Bit 13)	Bit = 0	Disabled (main loop operates)			
	Bit = 1	Enabled (main loop shuts down)			
	Phase Detector RE	Ference source			
(Bit 14)	Bit = 0	Reference Divider			
	Bit = 1	REF pin			
	Phase Detector Fe	edBacK source			
(Bit 15)	Bit = 0	Feedback Divider			
(Dit 13)	Bit = 1	FBK pin			
	FeedBacK Divider	SouRCe			
	Bit 39 = 0 Bit 38 = 0	Post Divider Output			
FBKDSRC[1:0]	Bit $39 = 0$ Bit $38 = 1$	FBK pin			
(Bits 39-38)	Bit $39 = 1$ Bit $38 = 0$	VCO Output (Post Divider Input)			
	Bit $39 = 1$ Bit $38 = 1$	FBK pin			
	EXTernal Loop Filter select				
EXTLF	Bit = 0	Internal Loop Filter			
(Bit 42)	Bit = 1	FXTI F pin			
	OSCillator TYPe				
OSCTYPE	Bit = 0	Low Phase Jitter Oscillator			
(Bit 45)	Bit = 1	ES6031 Compatible Oscillator			
	OUTput MUltipleXer select				
	Bit 47 = 0 Bit 46 = 0	Main Loop PLL (VCO Output)			
OUTMUX[1:0]	Bit 47 = 0 Bit 46 = 1	Reference Divider Output			
(Bits 47-40)	Bit 47 = 1 Bit 46 = 0	Phase Detector Input			
	Bit 47 = 1 Bit 46 = 1	VCXO Output			
CPI	clock GobBLer co	ntrol			
(Bit 18)	Bit = 0	No Clock Phase Adjust			
	Bit = 1	Clock Phase Delay			
	CLKP/CLKN output	t mode			
CMOS	Rit _ 0	PECL Output			
(Bit 60)		(positive-ECL output drive)			
(=	Bit = 1	CMOS Output /			

Table 5: LOCK/IPRG Pin Configuration Bits

Name	Description	Description			
STAT[1:0] (Bits 63-62)	Crystal Loop Lo Main Loop Pha (see also Table	Crystal Loop Lock STATus Mode / Main Loop Phase Align STATus mode (see also Table 6)			
	Bit 63 = 0 Bit 62 = 0	Crystal Loop Lock status: Locked or Unlocked			
	Bit 63 = 0 Bit 62 = 1	Crystal Loop Lock status: Out of Range High or Low			
	Bit 63 = 1 Bit 62 = 0	Main Loop Phase Align status			
	Bit 63 = 1 Bit 62 = 1	Feedback Divider output			

Table 6: Lock Status

CMOS	STAT [1]	STAT [0]	LOCK / IPRG PIN	STAT[1] Read	Status
1	0	0	1	1	Locked
1 0	0	0	0	Unlocked	
1	0	0 1	0	0	Out-of-Range: Low
			1	1	Out-of-Range: High

Table 7: Main Loop Tuning Bits

Name	Description			
	VCO SPeeD range select (see Table 16)			
(Bit 44)	Bit = 0	High Speed Range		
()	Bit = 1	Low Speed Range		
	Main Loop Charge Pur	np current		
	Bit 41 = 0 Bit 40 = 0	Current = 1.5µA		
MLCP[1:0] (Bits 41-40)	Bit 41 = 0 Bit 40 = 1	Current = 5µA		
	Bit 41 = 1 Bit 40 = 0	Current = 8µA		
	Bit 41 = 1 Bit 40 = 1	Current = 24µA		
	Loop Filter Time Constant (internal)			
(Bit 43)	Bit = 0	Short Time Constant: 13.5µs		
	Bit = 1	Long Time Constant: 135µs		

Table 8: Divider Control Bits

Name	Description				
REFDIV[11:0] (Bits 11-0)	REFerence DIVider (N _R)				
	FeedBacK DIVider (N _F)				
(Bits 37-24)	FBKDIV[2:0]	A-Counter Value			
	FBKDIV[13:3]	M-Counter Value			
	POST Divider #1 (N _{P1})				
	Bit 17 = 0 Bit 16 = 0	Divide by 1			
POST1[1:0] (Bits 17-16)	Bit 17 = 0 Bit 16 = 1	Divide by 2			
	Bit 17 = 1 Bit 16 = 0	Divide by 4			
	Bit 17 = 1 Bit 16 = 1	Divide by 8			
	POST Divider #2 (N _{P2})				
	Bit 19 = 0 Bit 18 = 0	Divide by 1			
POST2[1:0] (Bits 19-18)	Bit 19 = 0 Bit 18 = 1	Divide by 3			
	Bit 19 = 1 Bit 18 = 0	Divide by 5			
	Bit 19 = 1 Bit 18 = 1	Divide by 4			
	POST Divider #3 (N _{P3})				
	Bit 21 = 0 Bit 20 = 0	Divide by 1			
POST3[1:0] (Bits 21-20)	Bit 21 = 0 Bit 20 = 1	Divide by 3			
	Bit 21 = 1 Bit 20 = 0	Divide by 5			
	Bit 21 = 1 Bit 20 = 1	Divide by 4			
Reserved (0) (Bits 23-22)	Set these reserved bits to 0				

Table 9: Crystal Loop Tuning Bits

Name	Description				
	Crystal Loop Charge Pump current				
XLCP[1:0]	Bit 53 = 0 Bit 52 = 0	Current = 1.5µA			
	Bit 53 = 0 Bit 52 = 1	Current = 5µA			
(Bit 53 = 1 Bit 52 = 0	Current = 8µA			
	Bit 53 = 1 Bit 52 = 1	Current = 24µA			
XLROM[2:0] (Bits 51-49)	Crystal Loop Divider ROM select and Crystal Oscillator Power-Down (see Error! Reference source not found.)				
XLVTEN (Bit 61)	Crystal Loop Voltage fine Tune ENable				
	Bit = 0	Disabled (fine tune is inactive)			
(2.001)	Bit = 1	Enabled (fine tune is active)			
	Crystal Loop SWAP polarity				
XLSWAP	Bit = 0	Use with an external VCXO that <i>increases</i> in frequency in response to an <i>increasing</i> voltage at the XTUNE pin.			
(Bit 54)	Bit = 1	Use with a VCXO that <i>increases</i> in frequency in response to a <i>decreasing</i> voltage at the XTUNE pin. Use this setting for Internal VCXO			
	Crystal Loop Power Down Enable				
XLPDEN	Bit = 0	Disabled (crystal loop operates)			
(Bit 55)	Bit = 1	Enabled (crystal loop is powered down)			
XCT[3:0] (Bits 59-56)	Crystal Coarse Tune (see Table 11)				

Table 10: Crystal Loop Control ROM

XLROM [2]	XLROM [1]	XLROM [0]	VCXO Divider	Crystal Frequency (MHz)		
0	0	0	1	-		
0	0	1	3072	24.576		
0	1	0	3156	25.248		
0	1	1	2430	19.44		
1	0	0	2500	20.00		
1	0	1	4000	32.00		
1	1	0	3375	27.00		
1	1	1	Crystal oscillator power-down			

6.1 VCXO Coarse Tune

The VCXO may be coarse tuned by a programmable adjustment of the crystal load capacitance via XCT[3:0]. The actual amount of frequency warping caused by the tuning capacitance will depend on the crystal used. The VCXO tuning capacitance includes an external 6pF load capacitance (12pF from the XIN pin to ground and 12pF from the XOUT pin to ground). The fine tuning capability of the VCXO can be enabled by setting the XLVTEN bit to a logic-one, or disabled by setting the bit to a logic-zero.

Table 11: VCXO Coarse Running Capacitance

ХСТ[3]	ХСТ[2]	ХСТ[1]	ХСТ[0]	VCXO Tuning Capacitance (pf)
0	0	0	0	10.00
0	0	0	1	10.84
0	0	1	0	11.69
0	0	1	1	12.53
0	1	0	0	13.38
0	1	0	1	14.22
0	1	1	0	15.06
0	1	1	1	15.91
1	0	0	0	16.75
1	0	0	1	17.59
1	0	1	0	18.43
1	0	1	1	19.28
1	1	0	0	20.13
1	1	0	1	20.97
1	1	1	0	21.81
1	1	1	1	22.66

7.0 Electrical Specifications

Table 12: Absolute Maximum Ratings

Parameter	Symbol	Min.	Max.	Units
Supply Voltage, dc (V_{SS} = ground)	V _{DD}	V _{ss} -0.5	7	V
Input Voltage, dc	Vı	V _{SS} -0.5	V _{DD} +0.5	V
Output Voltage, dc	Vo	V _{SS} -0.5	V _{DD} +0.5	V
Input Clamp Current, dc (V _I < 0 or V _I > V _{DD})	I _{IK}	-50	50	mA
Output Clamp Current, dc ($V_1 < 0$ or $V_1 > V_{DD}$)	I _{ок}	-50	50	mA
Storage Temperature Range (non-condensing)	Ts	-65	150	°C
Ambient Temperature Range, Under Bias	T _A	-55	125	°C
Junction Temperature	TJ		150	°C
Lead Temperature (soldering, 10s)			260	°C
Input Static Discharge Voltage Protection (MIL-STD 883E, Method 3015.7)			2	kV

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. These conditions represent a stress rating only, and functional operation of the device at these or any other conditions above the operational limits noted in this specification is not implied. Exposure to maximum rating conditions for extended conditions may affect device performance, functionality, and reliability.



CAUTION: ELECTROSTATIC SENSITIVE DEVICE

Permanent damage resulting in a loss of functionality or performance may occur if this device is subjected to a high-energy electrostatic discharge.

Table 13: Operating Conditions

Parameter	Symbol	Conditions/Descriptions	Min.	Тур.	Max.	Units
Supply Voltage	V _{DD}	5V ± 10%	4.5	5	5.5	V
Ambient Operating Temperature Range	T _A		0		70	°C
Crystal Resonator Frequency	f _{XIN}		19.44	27	28	MHz
Crystal Resonator Load Capacitance	C _{XL}	Parallel resonant, AT cut		18		pF
Crystal Resonator Motional Capacitance	C _{XM}	Parallel resonant, AT cut		25		fF
Serial Data Transfer Rate		Standard mode	10	100	400	kb/s
PECL Mode Programming Current (LOCK/IPRG Pin High-Level Input Current)	I _{IH}	PECL Mode			15	mA
Output Driver Load Capacitance	CL				15	pF

Table 14: DC Electrical Specifications

Parameter	Symbol	Conditions/Description	Min.	Тур.	Max.	Units
Overall						
Supply Current, Dynamic, (with Loaded Outputs)	I _{DD}	f_{CLK} = 66MHz ; CMOS Mode, V_{DD} = 5.5V		100		mA
Supply Current, Static	I _{DDL}	$\begin{array}{l} SHUT = 1, \ XLROM[2:0] = 7, \ XLPDEN = 1 \\ V_{\text{DD}} = 5.5 V \end{array}$		12		mA
Serial Communication I/O (SDA, SCL)						
High-Level Input Voltage	V _{IH}	Outputs off	3.5		V _{DD} +0.3	V
Low-Level Input Voltage	V _{IL}	Outputs off	V _{SS} -0.3		1.5	V
Hysteresis Voltage *	V _{hys}	Outputs off		2		V
Input Leakage Current	lı –		-1		1	μA
Low-Level Output Sink Current (SDA)	I _{OL}	$V_{OL} = 0.4V$	20	32		mA
Tristate Output Current	Iz		-10		10	μA
Address Select Input (ADDR)						
High-Level Input Voltage	V _{IH}		2.4		V _{DD} +0.3	V
Low-Level Input Voltage	V _{IL}		V _{SS} -0.3		0.8	V
High-Level Input Current (pull-down)	I _{IH}	$V_{\text{IH}} = V_{\text{DD}} = 5.5 V$	5	16	30	μA
Low-Level Input Current	I _{IL}		-2		2	μA
Reference Frequency Input (REF, FBK)						
High-Level Input Voltage	V _{IH}		3.5		V _{DD} +0.3	V
Low-Level Input Voltage	V _{IL}		V _{SS} -0.3		1.5	V
Hysteresis Voltage	V _{hys}		500			mV
Input Leakage Current	l _l		-1		1	μA

Table 14: DC Electrical Specifications (Continued)

Parameter	Symbol	Conditions/Description	Min.	Туре.	Max.	Units
Loop Filter Input (EXTLF)						
Input Leakage Current	I,	EXTLF = 0	-1		1	μA
		V _o = 0.8V; EXTLF =1, MLCP[1:0] = 0		-1.5		
Link Lough Output Course Output		V _o = 0.8V; EXTLF =1, MLCP[1:0] = 1		-5		μΑ
High-Level Output Source Current	IOH	V _o = 0.8V; EXTLF =1, MLCP[1:0] = 2		-8		
		V _o = 0.8V; EXTLF =1, MLCP[1:0] = 3		-24		
		V _o = 4.2V; EXTLF =1, MLCP[1:0] = 0		1.5		
Low Lovel Output Sink Current	1	V _o = 4.2V; EXTLF =1, MLCP[1:0] = 1		5		A
Low-Level Output Sink Guitent	IOL	$V_0 = 4.2V$; EXTLF =1, MLCP[1:0] = 2		8		μΑ
		$V_0 = 4.2V$; EXTLF =1, MLCP[1:0] = 3		25		
Crystal Oscillator Input (XIN)						
Threshold Bias Voltage	V _{TH}		1.5	2.2	3.5	V
High-Level Input Current	I _{IH}	Outputs off; $V_{IH} = 5V$	10	24	30	mA
Low-Level Input Current	IL	Outputs off; $V_{IL} = 0V$	-10	-19	-30	mA
Crystal Loading Capacitance *	C _{L(xtal)}	As seen by an external crystal connected to XIN and XOUT; VCXO tuning disabled		10		pF
Input Loading Capacitance *	C _{L(XIN)}	As seen by an external clock driver on XOUT; XIN unconnected; VCXO disabled		20		pF
Crystal Oscillator Output (XOUT)						
High-Level Output Source Current	I _{он}	$V_{O} = 0V$, float XIN	-20	-30	-50	mA
Low-Level Output Sink Current	I _{OL}	$V_{O} = 5V$, float XIN	-20	-40	-50	mA
VCXO Tuning I/O (XTUNE)						
High-Level Input Voltage	V _{IH}	Lock Status: Out of Range HIGH	3.2		V _{DD} +0.3	V
Low-Level Input Voltage	VIL	Lock Status: Out of Range LOW	V _{SS} -0.3		0.3	V
Hysteresis Voltage	V _{hys}		1.0			V
Input Leakage Current	lı lı	XLPDEN = 0	-1		1	μA
		V _o = 0.8V; XLCP[1:0] = 0		-1.5		
High-Level Output Source Current	Ь	V _o = 0.8V; XLCP[1:0] = 1		-5		
	.04	V _o = 0.8V; XLCP[1:0] = 2		-8		μυτ
		V _o = 0.8V; XLCP[1:0] = 3		-24		
		V _o = 4.2V; XLCP[1:0] = 0		1.5		
Low-Level Output Sink Current	la	V _o = 4.2V; XLCP[1:0] = 1		5		μА
	-01	V ₀ = 4.2V; XLCP[1:0] = 2		8		μι
		V _o = 4.2V; XLCP[1:0] = 3		25		
Lock Indicator / PECL Current Program I/	O (LOCK/IPF	RG)				
Low-Level Input Current	I _{IL}	PECL Mode	-1		1	μA
High-Level Output Source Current	I _{ОН}	CMOS Mode; $V_0 = 2.4V$	-25	-38		mA
Low-Level Output Sink Current	I _{OL}	CMOS Mode; $V_0 = 0.4V$	5	9		mA
Output Impedance *	Z _{OH}	$V_{O} = 0.5 V_{DD}$; output driving high		66		Ω
	Z _{OL}	$V_{O} = 0.5 V_{DD}$; output driving low		76		
Short Circuit Source Current *	I _{SCH}	$V_0 = 0V$; shorted for 30s, max.		-47		mA
Short Circuit Sink Current *	I _{SCL}	$V_{\rm O}$ = 5V; shorted for 30s, max.		47		mA

Table 14: DC Electrical Specifications (Continued)

Parameter	Symbol	Conditions/Description	Min.	Тур.	Max.	Units				
Clock Outputs, CMOS Mode (CLKN, CLKP)										
High-Level Output Source Current	I _{OH}	$V_{\rm O} = 2.4 V$	-45	-68		mA				
Low-Level Output Sink Current	I _{OL}	$V_{O} = 0.4V$	15	20		mA				
Output Impedance *	z _{OH}	$V_{O} = 0.5 V_{DD}$; output driving high		28		0				
	Z _{OL}	$V_{O} = 0.5 V_{DD}$; output driving low		33		52				
Short Circuit Source Current *	I _{SCH}	$V_0 = 0V$; shorted for 30s, max.		-100		mA				
Short Circuit Sink Current *	I _{SCL}	$V_0 = 5V$; shorted for 30s, max.		100		mA				
Clock Outputs, PECL Mode (CLKN, CLKP)										
IPRG Current to Output Current Ratio				1:4						
Low-Level Output Sink Current	I _{OL}	IPRG input current = 15mA		60		mA				
Tristate Output Current	lz		-10		10	μA				

Unless otherwise stated, $V_{DD} = 5.0V \pm 10\%$, no load on any output, and ambient temperature range $T_A = 0^{\circ}C$ to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. MIN and MAX characterization data are $\pm 3\sigma$ from typical. Negative currents indicate current flows out of the device.

Table 15: AC Timing Specifications

Parameter	Symbol	Conditions/Description	Clock (MHz)	Min.	Тур.	Max.	Units			
Overall										
Output Eroquopov *	4	CMOS Outputs				130	MU-			
Output Frequency	O(max)	PECL Outputs				230				
		Low Phase Jitter Oscillator (OSCTYPE = 0)								
		VCOSPD = 0		40		160				
	fuer	VCOSPD = 1		40		100	MH-7			
VOOTTequency	IVCO	FS6031 Compatible Oscillator (OSCTYPE =	1)				1011 12			
		VCOSPD = 0		40		230				
		VCOSPD = 1		40		140				
	A _{vco}	Low Phase Jitter Oscillator (OSCTYPE = 0)								
		VCOSPD = 0			125					
VCO Gain *		VCOSPD = 1			75					
VOO Gam		FS6031 Compatible Oscillator (OSCTYPE =	1)				IVII 12/ V			
		VCOSPD = 0			130					
		VCOSPD = 1			78					
Loop Filter Time Constant *		LFTC = 0			13.5					
Loop Thile Thine Constant		LFTC = 1 135					μο			
Rise Time *	tr	CMOS Outputs, $V_{O} = 0.5V$ to 4.5V; $C_{L} = 15p$	F		1.1		ns			
Fall Time *	t _f	CMOS Outputs, V_{O} = 4.5V to 0.5V; C_{L} = 15p	F		0.8		ns			
Lock Time (Main Loop) *		Frequency Synthesis			200		μS			
Lock Time (Main Loop)		Line Locked Modes (8kHz reference)			10		ms			
Disable Time *		From falling edge of SCL for the last data bit (SHUT = 1 to 0) to output locked			10		μS			

Table 15: AC Specifications (Continued)

Parameter	Symbol	Conditions/Description Clock (MHz)		Min.	Тур.	Max.	Units
Divider Modulus			-				
Feedback Divider	N _F	FBKDIV[13:0] (See also Table 2)		8		16383	
Reference Divider	N _R	REFDIV[11:0]		1		4095	
	N _{P1}	POST1[1:0] (See also Table 8)		1		8	
Post Divider	N _{P2}	POST2[1:0] (See also Table 8)		1		5	
	N _{P3}	POST3[1:0] (See also Table 8)		1		5	
Clock Output (CLKP, CLKN)							
Duty Cycle *		Ratio of pulse width (as measured from rising edge to next falling edge at 2.5V) to one clock period	100	47		54	%
Jitter, Long Term $(\sigma_y(\tau))$ *	t _{j(LT)}	Rising edges 50ms apart at 2.5V, relative to an ideal clock, $C_L=15pF$, $f_{REF}=8kHz$, $N_R=1$, $N_F=193$, $N_{P*}=64$, $C_{LF}=0.054\mu F$, $R_{LF}=15.7k\Omega$, $C_{LP}=1800pF$, OSCTYPE=0, MLCP=3, XLROM=7	1.544		270		
		Rising edges 50ms apart at 2.5V, relative to an ideal clock, $C_L=15pF$, $f_{REF}=15kHz$, $N_R=1$, $N_F=800$, $N_{Px}=10$, $C_{LF}=0.0246\mu F$, $R_{LF}=15.7k\Omega$, $C_{LP}=820pF$, OSCTYPE=0, MLCP=3, XLROM=7	12.00		160		
		On rising edges 5ms apart at 2.5V relative to an ideal clock, $C_L=15pF,f_{REF}=31.5kHz,N_R=1,N_F=799,N_{Px}=4,C_L=0.015\mu F,R_{LF}=15.7k\Omega,C_{LP}=470pF,OSCTYPE=0,MLCP=3,XLROM=7$	25.175		100		ps
		On rising edges 500 μ s apart at 2.5V relative to an ideal clock, $C_L=15pF,$ CMOS mode, $f_{XIN}=27MHz,$ $N_F=200,$ $N_R=27,$ $N_{Px}=2$			30		
		On rising edges 500 μs apart at 2.5V relative to an ideal clock, $C_L{=}15pF,$ PECL mode, $f_{XIN}{=}27MHz,$ $N_F{=}200,$ $N_R{=}27,$ $N_{Px}{=}1$	200		30		
Jitter, Period (peak-peak) *	t _{j(ΔP)}	From rising edge to next rising edge at 2.5V, C _L =15pF, f _{REF} =8kHz, N _R =1, N _F =193, N _{Px} =64, C _{LF} =0.054 μ F, R _{LF} =15.7k Ω , C _{LP} =1800pF, OSCTYPE=0, MLCP=3, XLROM=7	1.544		140		
		From rising edge to next rising edge at 2.5V, CL=15pF, f _{REF} =15kHz, N _R =1, N _F =800, N _{Px} =10, CL _F =0.0246 μ F, RL _F =15.7k Ω , CL _P =820pF, OSCTYPE=0, MLCP=3, XLROM=7	12.00		130		
		From rising edge to next rising edge at 2.5V, C _L =15pF, f_{REF} =31.5kHz, N _R =1, N _F =799, N _P =4, C _L F=0.015µF, R _L F=15.7k\Omega, C _L P=470pF, OSCTYPE=0, MLCP=3, XLROM=7	25.175		105		ps
		From rising edge to next rising edge at 2.5V, $C_L = 15 p F, CMOS mode, f_{XIN} = 27 MHz, N_F = 200, N_R = 27, N_{Px} = 2$	100		340		
		From rising edge to next rising edge at 2.5V, CL=15pF, PECL mode, f_{XIN} =27MHz, $N_{\rm F}$ =200, $N_{\rm R}$ =27, $N_{\rm Px}$ =1	200		270		

Unless otherwise stated, $V_{DD} = 5.0V \pm 10\%$, no load on any output, and ambient temperature range $T_A = 0^{\circ}$ C to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data at $T_A = 27^{\circ}$ C and are not production tested to any specific limits. MIN and MAX characterization data are $\pm 3\sigma$ from typical.

Table 16: Serial Interface Timing Specifications

Parameter	Symbol	Conditions/Description	Min.	Max.	Units
Clock frequency	f _{SCL}	SCL	0	400	kHz
Bus free time between STOP and START	t _{BUF}		4.7		μS
Set up time, START (repeated)	t _{su:STA}		4.7		μS
Hold time, START	t _{hd:STA}		4.0		μS
Set up time, data input	t _{su:DAT}	SDA	250		ns
Hold time, data input	t _{hd:DAT}	SDA	0		μS
Output data valid from clock	t _{AA}	Minimum delay to bridge undefined region of the falling edge of SCL to avoid unintended START or STOP		3.5	μS
Rise time, data and clock	t _R	SDA, SCL		1000	ns
Fall time, data and clock	tF	SDA, SCL		300	ns
High time, clock	t _{HI}	SCL	4.0		μS
Low time, clock	t _{LO}	SCL	4.7		μS
Set up time, STOP	t _{su:STO}		4.0		μs

Unless otherwise stated, $V_{DD} = 5.0V \pm 10\%$, no load on any output, and ambient temperature range $T_A = 0^{\circ}C$ to 70°C. Parameters denoted with an asterisk (*) represent nominal characterization data and are not production tested to any specific limits. MIN and MAX characterization data are $\pm 3\sigma$ from typical.